

1 – 10 (Canceled).

11. (Currently Amended) A method of manufacturing an integrated circuit chip structure comprising:
- supplying an integrated circuit chip; and
 - patterning a conductive polymer directly on an exterior conductor level of said integrated circuit chip,
- wherein said patterning produces passive devices.
12. (Original) The method in claim 11, wherein said passive devices comprise RF devices.
13. (Original) The method in claim 11, wherein said passive devices comprise at least one of resistors, capacitors, and inductors.
14. (Original) The method in claim 13, wherein said resistors comprise serpentine resistors.
15. (Original) The method in claim 13, wherein said capacitors comprise interdigitated capacitors.
16. (Original) A method of manufacturing an integrated circuit chip structure comprising:
- patterning a conductive polymer on a substrate; and
 - bonding said patterned conductive polymer to an integrated circuit chip,
- wherein said patterning produces passive devices.
17. (Original) The method in claim 16, wherein said passive devices comprise RF devices.

18. (Original) The method in claim 16, wherein, said passive devices comprise at least one of resistors, capacitors, and inductors.
19. (Original) The method in claim 18, wherein said resistors comprise serpentine resistors.
20. (Original) The method in claim 18, wherein said capacitors comprise interdigitated capacitors.
21. (New) A method of manufacturing an integrated circuit chip structure comprising:
supplying an integrated circuit chip; and
patterning a conductive polymer directly on an exterior conductor level of said integrated circuit chip,
wherein said patterning produces passive devices, and
wherein said patterning is performed such that said passive devices comprise an integral part of said integrated circuit chip.
22. (New) The method in claim 21, wherein said passive devices comprise RF devices.
23. (New) The method in claim 21, wherein said passive devices comprise at least one of resistors, capacitors, and inductors.
24. (New) The method in claim 23, wherein said resistors comprise serpentine resistors.
25. (New) The method in claim 23, wherein said capacitors comprise interdigitated capacitors.